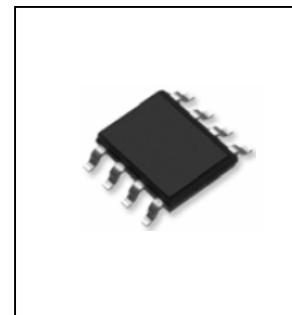


## P-Channel Enhancement Mode Power MOSFET

### Description

The 4953 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a load switch or in PWM applications.

**4953**



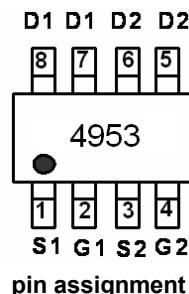
SOP-8 top view

### General Features

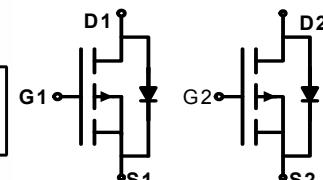
- $V_{DS} = -30V, I_D = -5.1A$
- $R_{DS(ON)} < 105m\Omega @ V_{GS}=-4.5V$
- $R_{DS(ON)} < 55m\Omega @ V_{GS}=-10V$
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

### Application

- PWM applications
- Load switch
- Power management



pin assignment



Schematic diagram

### Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	-4.9	A
Drain Current-Pulsed (Note 1)	$I_{DM}$	-20	A
Maximum Power Dissipation	$P_D$	2	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	°C

### Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	50	°C/W
--	-----------------	----	------

### Electrical Characteristics ( $T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-30	-33		V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-24V, V_{GS}=0V$			-1	$\mu A$

# 4953

Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V			±100	nA
<b>On Characteristics</b> <small>(Note 3)</small>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-1	-1.6	-3	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-5.1A		48	55	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-4.2A		73	105	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =-15V, I <sub>D</sub> =-4.5A	4	7		S
<b>Dynamic Characteristics</b> <small>(Note 4)</small>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, F=1.0MHz		520		PF
Output Capacitance	C <sub>oss</sub>			130		PF
Reverse Transfer Capacitance	C <sub>rss</sub>			70		PF
<b>Switching Characteristics</b> <small>(Note 4)</small>						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =-15V, ID=-1A, V <sub>GS</sub> =-10V, R <sub>GEN</sub> =6Ω		7		nS
Turn-on Rise Time	t <sub>r</sub>			13		nS
Turn-Off Delay Time	t <sub>d(off)</sub>			14		nS
Turn-Off Fall Time	t <sub>f</sub>			9		nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-15V, I <sub>D</sub> =-5.1A, V <sub>GS</sub> =-10V		12		nC
Gate-Source Charge	Q <sub>gs</sub>			2.2		nC
Gate-Drain Charge	Q <sub>gd</sub>			3		nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage <small>(Note 3)</small>	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>s</sub> =-1.7A			-1.2	V

**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

# 4953

## Typical Electrical and Thermal Characteristics

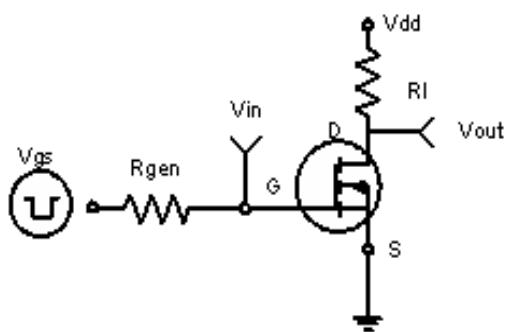


Figure 1:Switching Test Circuit

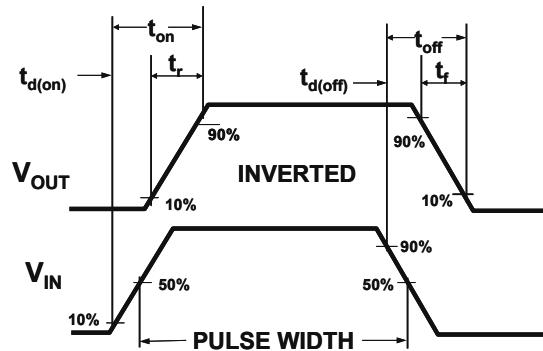


Figure 2:Switching Waveforms

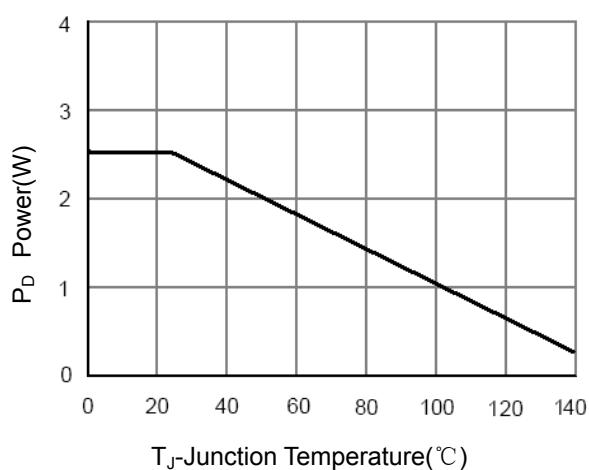
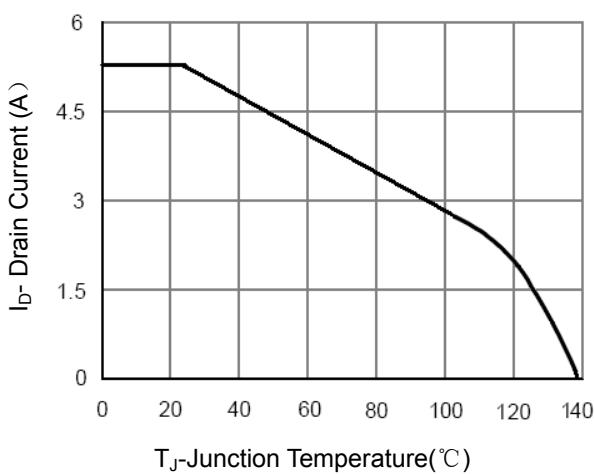


Figure 3 Power Dissipation



T<sub>J</sub>-Junction Temperature(°C)

Figure 4 Drain Current

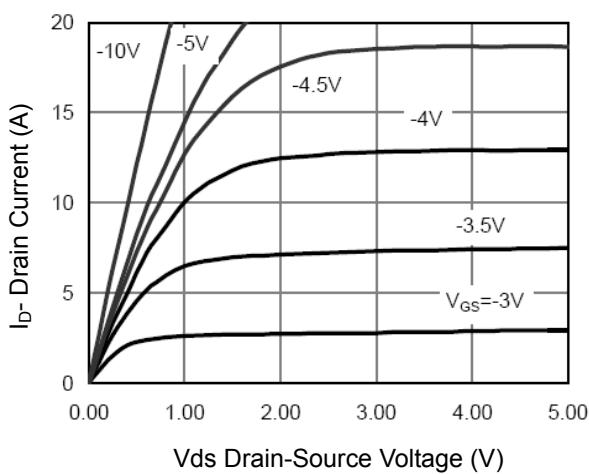


Figure 5 Output Characteristics

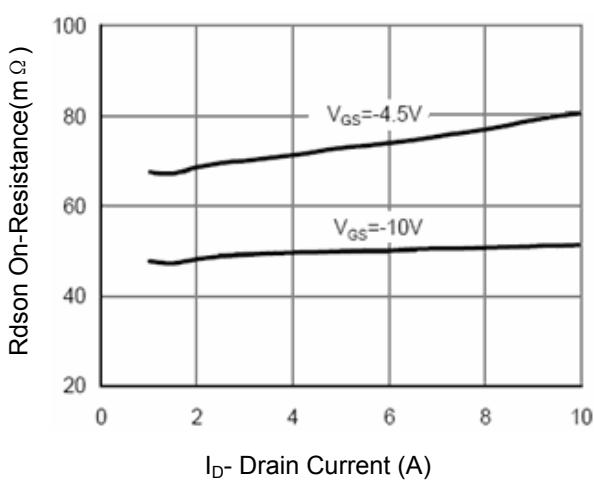


Figure 6 Drain-Source On-Resistance

4953

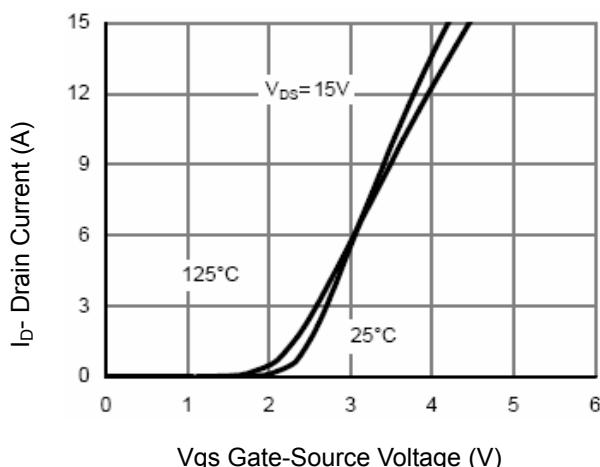


Figure 7 Transfer Characteristics

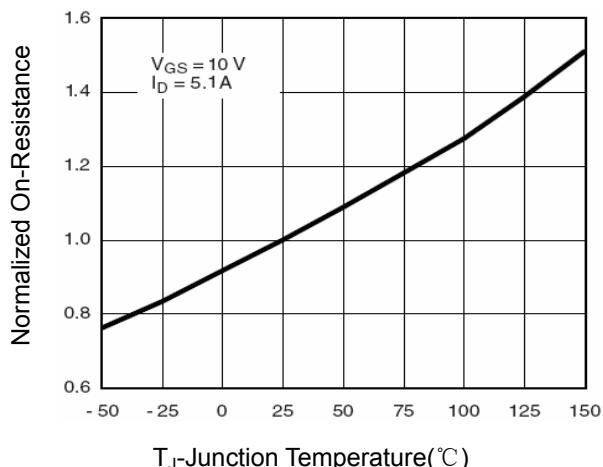


Figure 8 Drain-Source On-Resistance

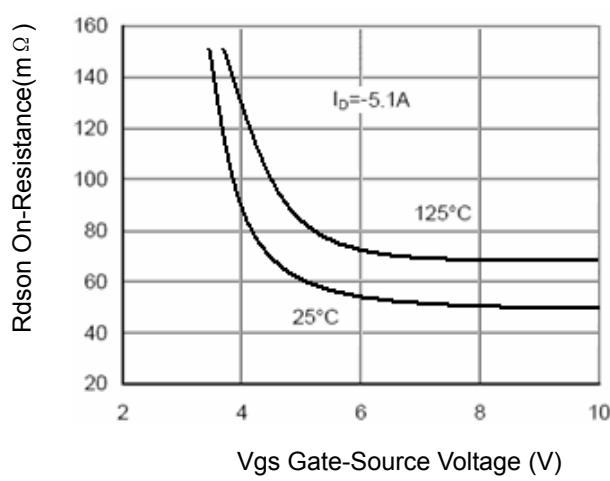


Figure 9  $R_{DS(on)}$  vs  $V_{GS}$

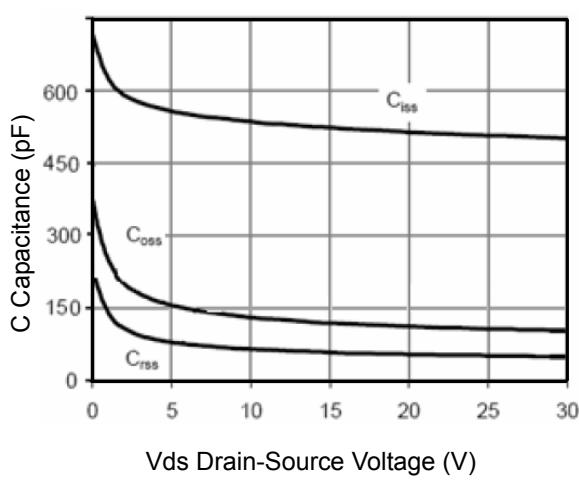


Figure 10 Capacitance vs  $V_{DS}$

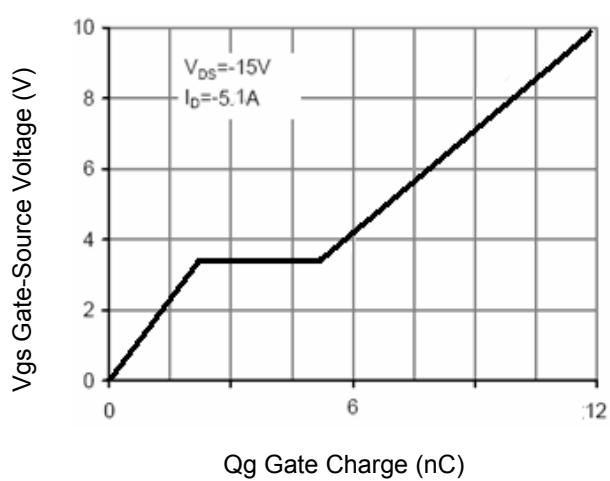


Figure 11 Gate Charge

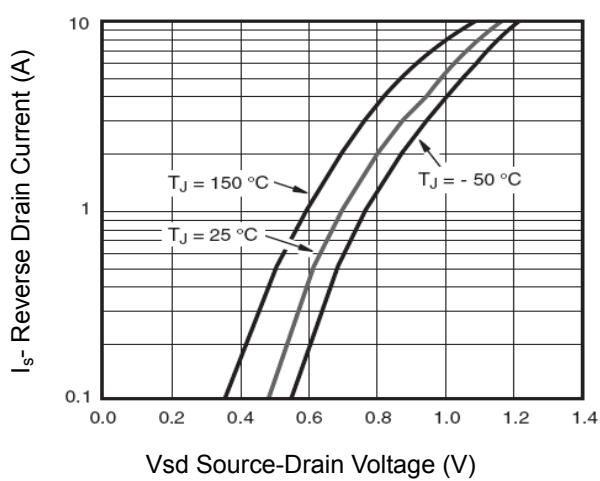
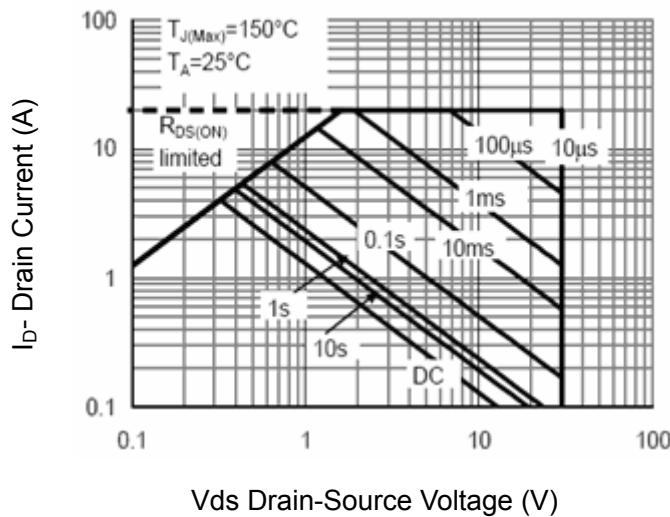
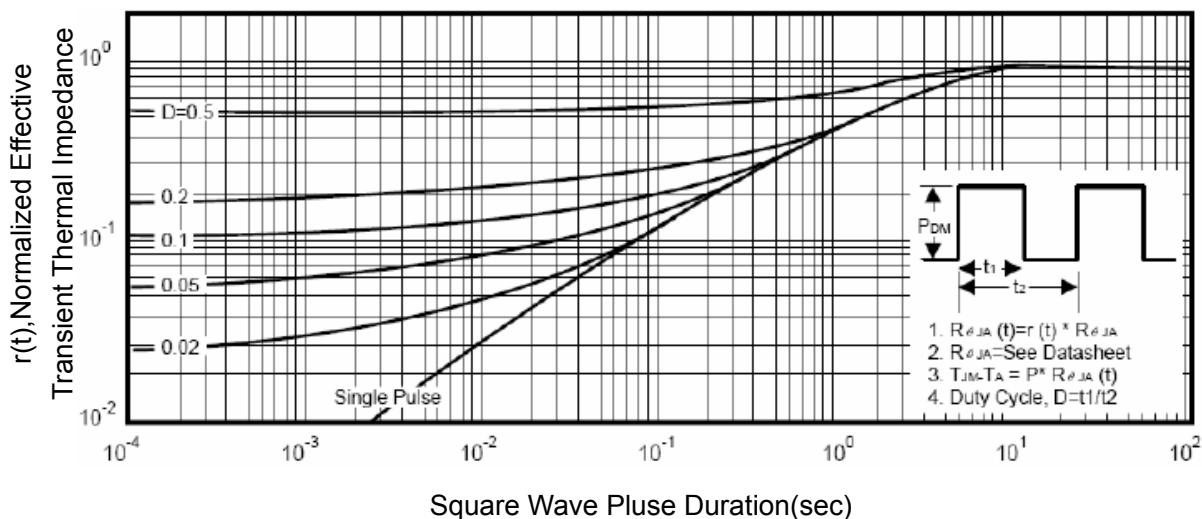


Figure 12 Source-Drain Diode Forward

4953



**Figure 13 Safe Operation Area**



**Figure 14 Normalized Maximum Transient Thermal Impedance**

# X-ON Electronics

Largest Supplier of Electrical and Electronic Components

***Click to view similar products for MOSFET category:***

***Click to view products by Hottech manufacturer:***

Other Similar products are found below :

[614233C](#) [648584F](#) [NTNS3A92PZT5G](#) [IRFD120](#) [IRFF430](#) [JANTX2N5237](#) [2N7000](#) [2SK2464-TL-E](#) [FCA20N60\\_F109](#) [FDZ595PZ](#) [AOD464](#)  
[2SK2267\(Q\)](#) [2SK2545\(Q,T\)](#) [405094E](#) [423220D](#) [MIC4420CM-TR](#) [VN1206L](#) [614234A](#) [715780A](#) [SSM6J414TU,LF\(T](#) [751625C](#)  
[IPP60R600P6XKSA1](#) [RJK60S5DPK-M0#T0](#) [PSMN4R2-30MLD](#) [TK31J60W5,S1VQ\(O](#) [2SK2614\(TE16L1,Q\)](#) [DMN1017UCP3-7](#)  
[EFC2J004NUZTDG](#) [FCAB21350L1](#) [P85W28HP2F-7071](#) [DMN1053UCP4-7](#) [NTE2384](#) [NTE2969](#) [NTE6400A](#) [DMN61D9UWQ-13](#)  
[US6M2GTR](#) [DMN31D5UDJ-7](#) [SSM6P54TU,LF](#) [DMP22D4UFO-7B](#) [IPS60R3K4CEAKMA1](#) [DMN1006UCA6-7](#) [DMN16M9UCA6-7](#)  
[STF5N65M6](#) [STU5N65M6](#) [C3M0021120D](#) [DMN13M9UCA6-7](#) [BSS340NWH6327XTSA1](#) [MCM3400A-TP](#) [DMTH10H4M6SPS-13](#)  
[IRF40SC240ARMA1](#)